

## PNP SILICON AMPLIFIER TRANSISTOR

Qualified per MIL-PRF-19500/357

### Devices

<b>2N3634</b>	<b>2N3635</b>	<b>2N3636</b>	<b>2N3637</b>
<b>2N3634L</b>	<b>2N3635L</b>	<b>2N3636L</b>	<b>2N3637L</b>

### Qualified Level

**JAN**  
**JANTX**  
**JANTXV**  
**JANS**

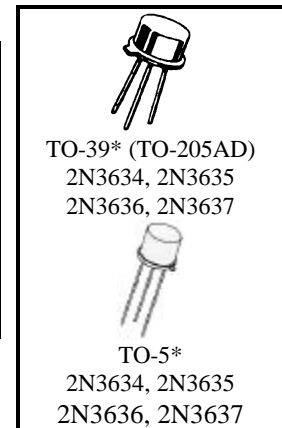
### MAXIMUM RATINGS

Ratings	Symbol	2N3634* 2N3635*	2N3636* 2N3637*	Unit
Collector-Emitter Voltage	$V_{CEO}$	140	175	Vdc
Collector-Base Voltage	$V_{CBO}$	140	175	Vdc
Emitter-Base Voltage	$V_{EBO}$	5.0		Vdc
Collector Current	$I_C$	1.0		Adc
Total Power Dissipation	$P_T$	@ $T_A = +25^{\circ}C^{(1)}$	1.0	W
		@ $T_C = +25^{\circ}C^{(2)}$	5.0	W
Operating & Storage Junction Temperature Range	$T_J, T_{stg}$	-65 to +200		$^{\circ}C$

\*Electrical characteristics for "L" suffix devices are identical to the "non L" corresponding devices

1) Derate linearly 5.71 mW/ $^{\circ}C$  for  $T_A > +25^{\circ}C$

2) Derate linearly 28.6 mW/ $^{\circ}C$  for  $T_C > +25^{\circ}C$



\*See appendix A for package outline

### ELECTRICAL CHARACTERISTICS ( $T_A = 25^{\circ}C$ unless otherwise noted)

Characteristics	Symbol	Min.	Max.	Unit
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#### OFF CHARACTERISTICS

Collector-Emitter Breakdown Current $I_C = 10$ mAdc	2N3634, 2N3635 2N3636, 2N3637	$V_{(BR)CEO}$	140 175	Vdc
Collector-Base Cutoff Current $V_{CB} = 100$ Vdc $V_{CB} = 140$ Vdc	2N3634, 2N3635	$I_{CBO}$	100 10	$\eta$ Adc $\mu$ Adc
Emitter-Base Cutoff Current $V_{EB} = 3.0$ Vdc $V_{EB} = 5.0$ Vdc		$I_{EBO}$	50 10	$\eta$ Adc $\mu$ Adc
Collector-Emitter Cutoff Current $V_{CE} = 100$ Vdc		$I_{CEO}$	10	$\mu$ Adc

